MOSFET – Power, N-Channel

100 V, 1.6 mΩ

NVCR4LS1D6N10MCA

Features

- Typical $R_{DS(on)}$ = 1.25 mΩ at V_{GS} = 10 V
- Typical $Q_{g(tot)}$ = 115 nC at V_{GS} = 10 V
- AEC−Q101 Qualified
- RoHS Compliant

DIMENSION (μm)

Die Size	6800 × 4150
Die Size (Sawn)	6780 ±15 × 4130 ±15
Source Attach Area	(6228 × 1873.1) × 2
Gate Attach Area	330 × 600
Die Thickness	101.6 ±19.1

Gate and Source: AlSiCu
Drain: Ti−NiV−Ag (back side of die)
Passivation: Polyimide
Wafer Diameter: 8 inch
Wafer Sawn on UV Tape
Bad Dice Identified in Inking
Gross Die Counts: 862

ORDERING INFORMATION

Device	Package
NVCR4LS1D6N10MCA	Wafer Sawn on Foil

RECOMMENDED STORAGE CONDITIONS

Temperature	22 to 28°C
RH	40 to 66%

The Chip is 100% Probed to Meet the Conditions and Limits Specified at T_J = 25°C.

Symbol	Parameter	Condition	Min	Typ	Max	Unit
BV_{DSS}	Drain to Source Breakdown Voltage	I_D = 250 μA, V_{GS} = 0 V	100	–	–	V
I_{DSS}	Drain to Source Leakage Current	V_{DS} = 100 V, V_{GS} = 0 V	–	–	10	μA
I_{GSS}	Gate to Source Leakage Current	V_{GS} = ±20 V, V_{DS} = 0 V	–	–	±100	nA
$V_{GS(th)}$	Gate to Source Threshold Voltage	V_{GS} = V_{DS}, I_D = 698 μA	2.0	–	4.0	V
*$R_{DS(on)}$	Bare Die Drain to Source On Resistance	I_D = 40 A, V_{GS} = 10 V	–	1.25	1.6	mΩ
*V_{SD}	Source to Drain Diode Voltage	I_{SD} = 40 A, V_{GS} = 0 V	–	–	1.3	V
E_{AS}	Single Pulse Drain−to−Source Avalanche Energy	L = 1.0 mH, I_{AS} = 39 A	760	–	–	mJ

*Accurate $R_{DS(on)}$, V_{SD} test at die level is not feasible as limited by the test contact precision attainable in a die form. The max $R_{DS(on)}$, V_{SD} specification is defined from the historical performance of the die in package but is not guaranteed by test in production. The die $R_{DS(on)}$ performance depends on the Source wire/ribbon bonding layout.

MOSFET MAXIMUM RATINGS in Reference to the NVBLS1D7N10MC electrical data in TOLL
(T_J = 25°C unless otherwise noted)

Symbol	Parameter	Ratings	Unit
V_{DSS}	Drain to Source Voltage	100	V
V_{GS}	Gate to Source Voltage	±20	V
I_D	Continuous Drain Current $R_{\theta JC}$ (V_{GS} = 10) (Note 1) T_C = 25°C T_C = 100°C	 265 187	A
E_{AS}	Single Pulse Avalanche Energy (Note 2)	760	mJ
P_D	Power Dissipation $R_{\theta JC}$	303	W
	Derate Above 25°C	2.02	W/°C
T_J, T_{STG}	Operating and Storage Temperature	−55 to +175	°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	0.49	°C/W
$R_{\theta JA}$	Maximum Thermal Resistance, Junction to Ambient (Note 3)	33	°C/W

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Current is limited by silicon.
2. Starting T_J = 25°C, L = 1.0 mH, I_{AS} = 39 A, V_{DD} = 100 V during inductor charging and V_{DD} = 0 V during time in avalanche.
3. $R_{\theta JA}$ is the sum of the junction−to−case and case−to−ambient thermal resistance, where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design, while $R_{\theta JA}$ is determined by the board design. The maximum rating presented here is based on mounting on a 650 mm^2 pad of 2oz copper.

ELECTRICAL CHARACTERISTICS in Reference to the NVBLS1D7N10MC electrical data in TOLL
(T_J = 25°C unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
OFF CHARACTERISTICS						
BV_{DSS}	Drain to Source Breakdown Voltage	I_D = 250 μA, V_{GS} = 0 V	100	–	–	V
I_{DSS}	Drain to Source Leakage Current	V_{DS} = 100 V, V_{GS} = 0 V	–	–	10	μA
I_{GSS}	Gate to Source Leakage Current	V_{GS} = ±20 V	–	–	±100	nA
ON CHARACTERISTICS						
$V_{GS(th)}$	Gate to Source Threshold Voltage	V_{GS} = V_{DS}, I_D = 698 μA	2.0	–	4.0	V
$R_{DS(on)}$	Drain to Source on Resistance	I_D = 80 A, V_{GS} = 10 V	–	1.5	1.8	mΩ
DYNAMIC CHARACTERISTICS						
C_{iss}	Input Capacitance	V_{DS} = 50 V, V_{GS} = 0 V, f = 1 MHz	–	9200	–	pF
C_{oss}	Output Capacitance		–	4600	–	pF
C_{rss}	Reverse Transfer Capacitance		–	79	–	pF
$Q_{g(ToT)}$	Total Gate Charge	V_{GS} = 10 V, V_{DS} = 50 V, I_D = 80 A	–	115	–	nC
$Q_{g(th)}$	Threshold Gate Charge		–	24	–	nC
Q_{gs}	Gate to Source Gate Charge		–	47	–	nC
Q_{gd}	Gate to Drain “Miller” Charge		–	16	–	nC
SWITCHING CHARACTERISTICS						
$t_{d(on)}$	Turn−On Delay	V_{DS} = 50 V, I_D = 80 A, V_G = 10 V, R_G = 6 Ω	–	48	–	ns
t_r	Rise Time		–	38	–	ns
$t_{d(off)}$	Turn−Off Delay		–	76	–	ns
t_f	Fall Time		–	31	–	ns
DRAIN−SOURCE DIODE CHARACTERISTIC						
V_{SD}	Source to Drain Diode Voltage	I_{SD} = 80 A, V_{GS} = 0 V	–	–	1.3	V
t_{rr}	Reverse Recovery Time	I_F = 62 A, dI_{SD}/dt = 100 A/μs	–	98	–	ns
Q_{rr}	Reverse Recovery Charge		–	160	–	nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL CHARACTERISTICS

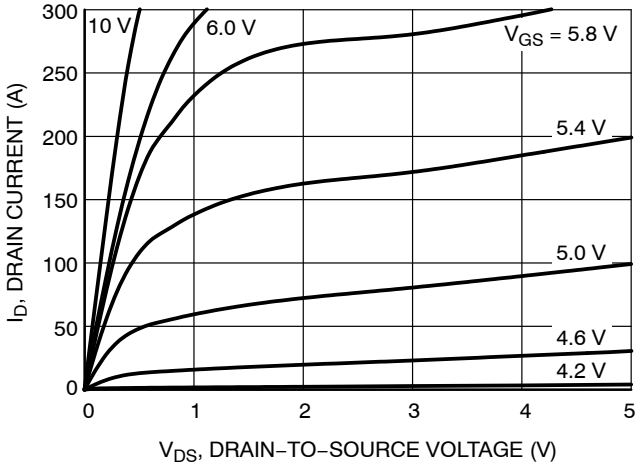

Figure 1. On−Region Characteristics

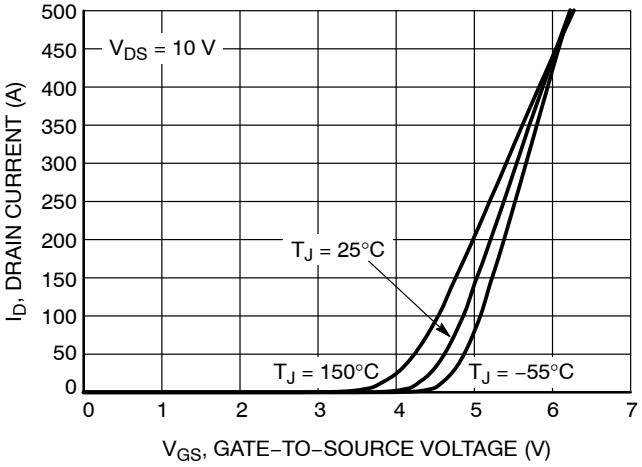

Figure 2. Transfer Characteristics

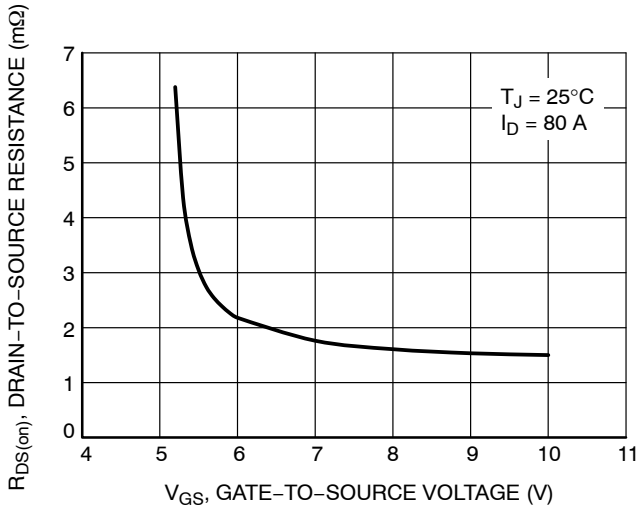

Figure 3. On−Resistance vs. Gate−to−Source Voltage

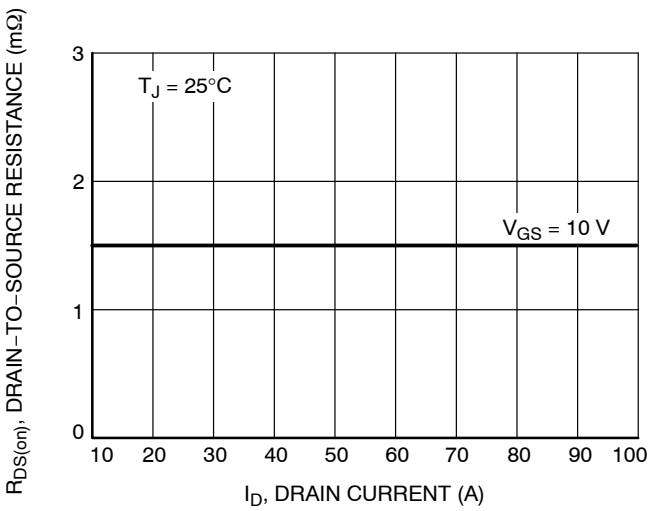

Figure 4. On−Resistance vs. Drain Current and Gate Voltage

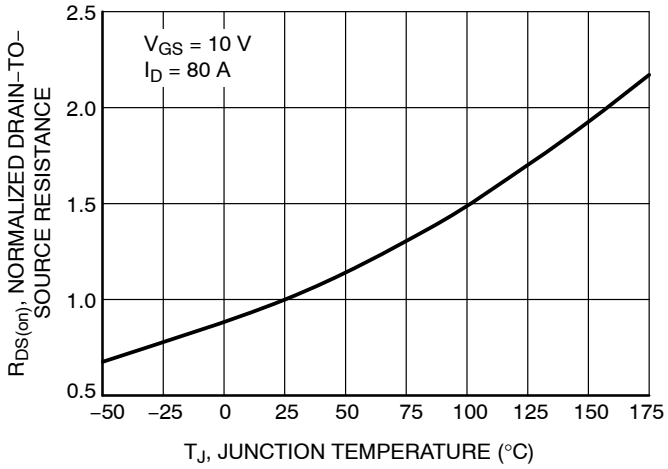

Figure 5. On−Resistance Variation with Temperature

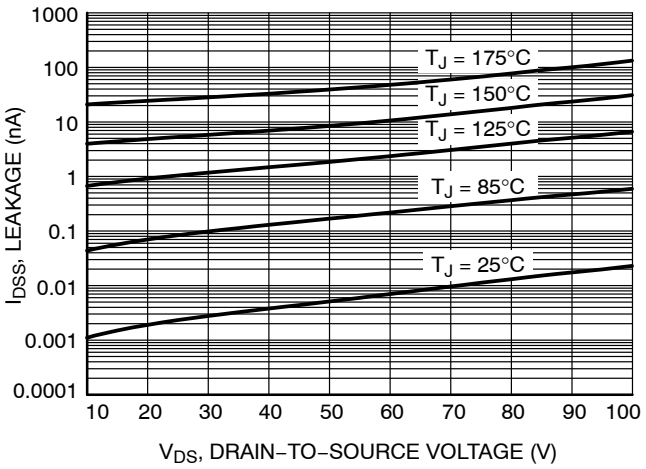

Figure 6. Drain−to−Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS

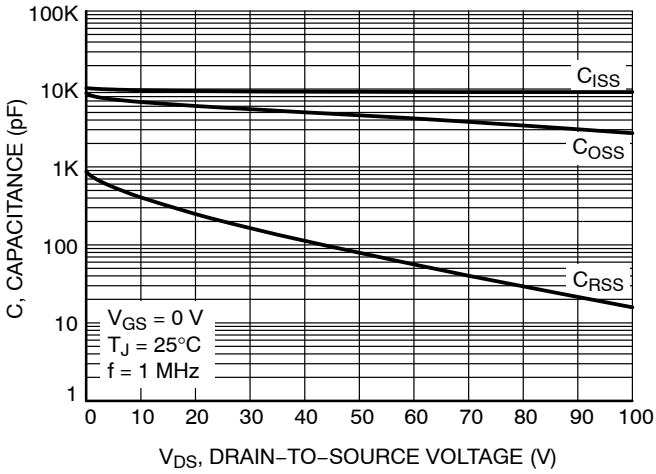

Figure 7. Capacitance Variation

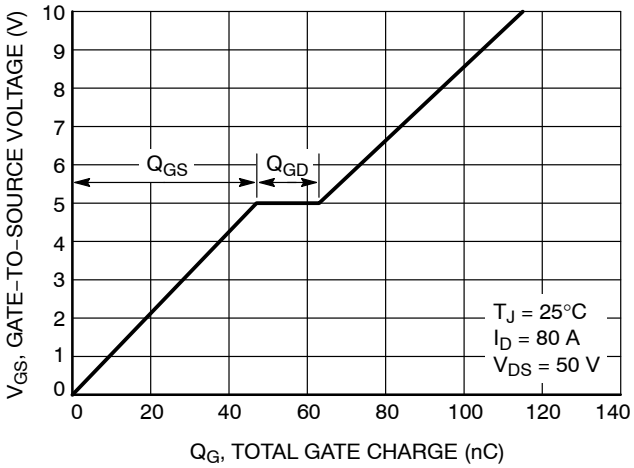

Figure 8. Gate−to−Source Voltage vs. Total Charge

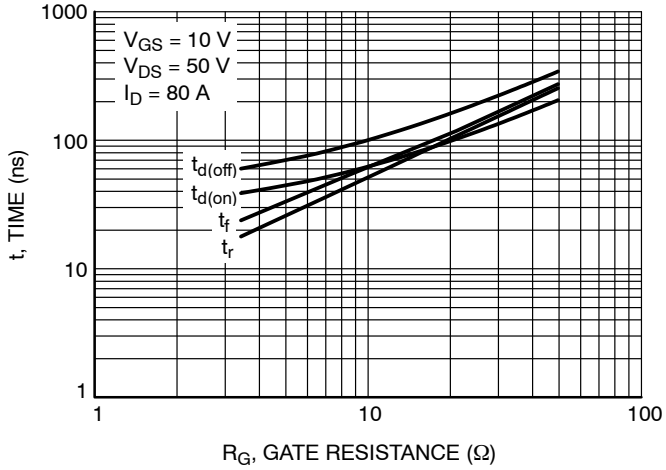

Figure 9. Resistive Switching Time Variation vs. Gate Resistance

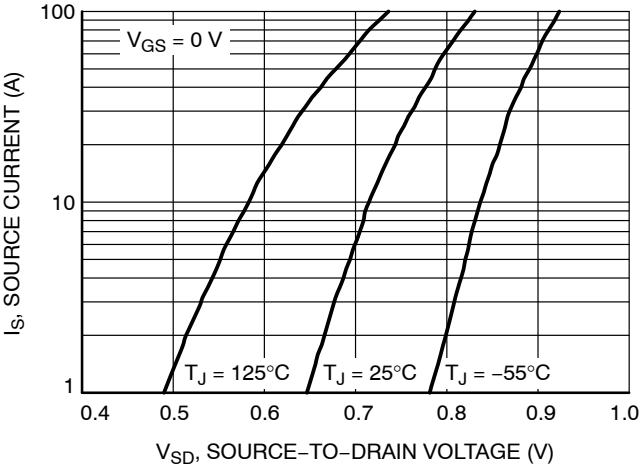

Figure 10. Diode Forward Voltage vs. Current

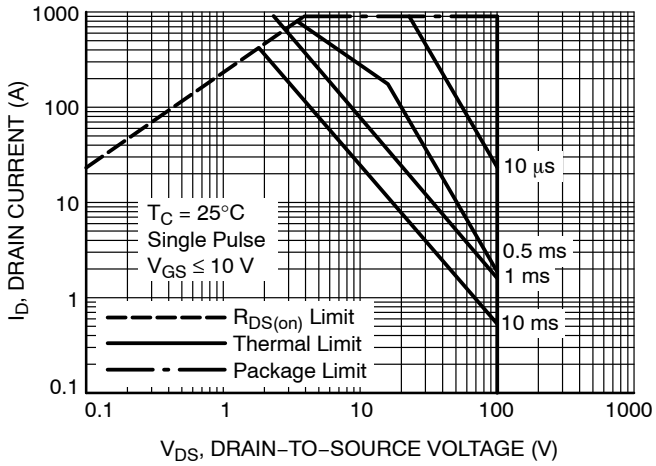

Figure 11. Maximum Rated Forward Biased Safe Operating Area

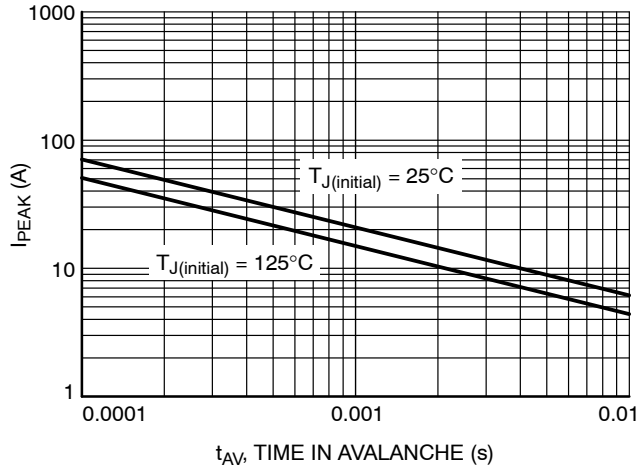

Figure 12. Maximum Drain Current vs. Time in Avalanche

TYPICAL CHARACTERISTICS

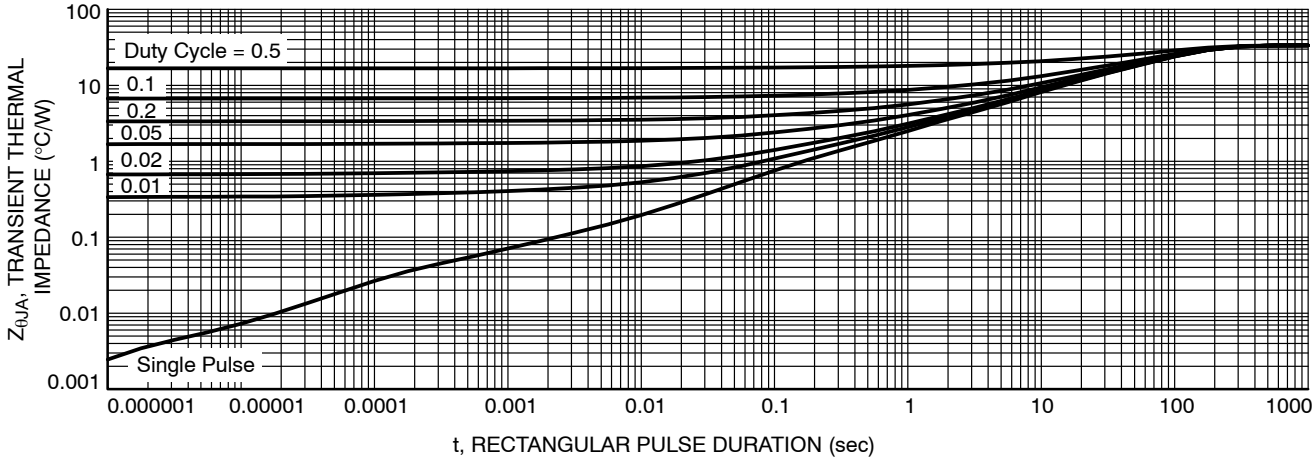

Figure 13. Transient Thermal Impedance

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Email Requests to: orderlit@onsemi.com

onsemi Website: www.onsemi.com

TECHNICAL SUPPORT
North American Technical Support:
Voice Mail: 1 800−282−9855 Toll Free USA/Canada
Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:
Phone: 00421 33 790 2910
For additional information, please contact your local Sales Representative

◊